

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please amend claims 1, 8, 9, 10, 17, 18, 19, 26 and 27 as follows:

LISTING OF CLAIMS:

1. (Currently Amended) A method of patterning a thin film comprising the steps of:

forming at least one strippable film on a whole surface of a thin film to be patterned;

etching patterning said at least one strippable film [[and]] together with said thin film to be patterned by using focused ion beam etching; and

removing the etched at least one strippable film.

2. (Original) The method as claimed in claim 1, wherein said at least one strippable film is an insulating organic film.

3. (Original) The method as claimed in claim 1, wherein said at least one strippable film is a conductive organic film.

4. (Original) The method as claimed in claim 1, wherein said at least one strippable film is an insulating organic film and a conductive film formed on said insulating organic film.

5. (Original) The method as claimed in claim 4, wherein said conductive film is a grounded film.

6. (Original) The method as claimed in claim 4, wherein said conductive film is a metallic material film.

7. (Original) The method as claimed in claim 4, wherein said conductive film is a conductive organic film.

8. (Currently Amended) A method of manufacturing a thin-film device, at least a part of a thin-film pattern being fabricated by using a thin-film patterning method, said thin film patterning method comprising the steps of:

forming at least one strippable film on a whole surface of a thin film to be patterned;

etching patterning said at least one strippable film and together with said thin film to be patterned by using focused ion beam etching; and

removing the etched at least one strippable film.

9. (Currently Amended) A method of manufacturing a thin-film magnetic head, at least a part of a thin-film pattern being fabricated by using a thin-film patterning method, said thin film patterning method comprising the steps of:

forming at least one strippable film on a whole surface of a thin film to be patterned;

etching patterning said at least one strippable film and together with said thin film to be patterned by using focused ion beam etching; and removing the etched at least one strippable film.

10. (Currently Amended) A method of patterning a thin film comprising the steps of:

forming at least one strippable film;

etching patterning said at least one strippable film by using focused ion beam etching;

forming a thin film to be patterned by using the etched at least one strippable film; and

removing the etched at least one strippable film.

11. (Original) The method as claimed in claim 10, wherein said at least one strippable film is an insulating organic film.

12. (Original) The method as claimed in claim 10, wherein said at least one strippable film is a conductive organic film.

13. (Previously Presented) The method as claimed in claim 10, wherein said at least one strippable film is formed as two layers including an insulating organic film and a conductive film formed on said insulating organic film.

14. (Original) The method as claimed in claim 13, wherein said conductive film is a grounded film.

15. (Original) The method as claimed in claim 13, wherein said conductive film is a metallic material film.

16. (Original) The method as claimed in claim 13, wherein said conductive film is a conductive organic film.

17. (Currently Amended) A method of manufacturing a thin-film device, at least a part of a thin-film pattern being fabricated by using a thin-film patterning method, said thin film patterning method comprising the steps of:

forming at least one strippable film;

etching patterning said at least one strippable film by using focused ion beam etching;

forming a thin film to be patterned by using the etched at least one strippable film; and

removing the etched at least one strippable film.

18. (Currently Amended) A method of manufacturing a thin-film magnetic head, at least a part of a thin-film pattern being fabricated by using a thin-film patterning method, said thin film patterning method comprising the steps of:

forming at least one strippable film;

etching patterning said at least one strippable film by using focused ion beam etching;

forming a thin film to be patterned by using the etched at least one strippable film; and

removing the etched at least one strippable film.

19. (Currently Amended) A method of patterning a thin film comprising the steps of:

forming at least one strippable film on a whole surface of a first thin film to be patterned;

etching patterning said at least one strippable film and together with said first thin film to be patterned by using focused ion beam etching;

forming a second thin film to be patterned using the etched at least one strippable film and said patterned first thin film to be patterned as a mask; and

removing the etched at least one strippable film.

20. (Original) The method as claimed in claim 19, wherein said at least one strippable film is an insulating organic film.

21. (Original) The method as claimed in claim 19, wherein said at least one strippable film is a conductive organic film.

22. (Previously Presented) The method as claimed in claim 19, wherein said at least one strippable film is formed as two layers including an insulating organic film and a conductive film formed on said insulating organic film.

23. (Original) The method as claimed in claim 22, wherein said conductive film is a grounded film.

24. (Original) The method as claimed in claim 22, wherein said conductive film is a metallic material film.

25. (Original) The method as claimed in claim 22, wherein said conductive film is a conductive organic film.

26. (Currently Amended) A method of manufacturing a thin-film device, at least a part of a thin-film pattern being fabricated by using a thin-film patterning method, said thin film patterning method comprising the steps of:

forming at least one strippable film on a whole surface of a first thin film to be patterned;

etching patterning said at least one strippable film and together with said first thin film to be patterned by using focused ion beam etching;

forming a second thin film to be patterned using the etched at least one strippable film and the etched first thin film to be patterned as a mask; and removing the etched at least one strippable film.

27. (Currently Amended) A method of manufacturing a thin-film magnetic head, at least a part of a thin-film pattern being fabricated by using a thin-film patterning method, said thin film patterning method comprising the steps of:

forming at least one strippable film on a whole surface of a first thin film to be patterned;

etching patterning said at least one strippable film and together with said first thin film to be patterned by using focused ion beam etching;

forming a second thin film to be patterned using the etched at least one strippable film and the etched first thin film to be patterned as a mask; and

removing the etched at least one strippable film.

AMENDMENTS TO THE DRAWINGS:

Attached is a replacement sheet to replace Figures 1a, 1b, 1c.